GAE GREAT AMERICAN ELECTROINCS

2N3020

Silicon NPN transistor 2N3020 is intended for high frequency amplifier applications.

Package Type: TO-39

ABSOLUTE MAXIMUM RATINGS (T_{CASE} = 25°C)

SYMBOL	Rating	VALUE	UNIT
V_{CER}	Collector-Emitter Voltage R_{EB}=3.0 KΩ	120	Vdc
V_{CEO}	Collector-Emitter Voltage	90	Vdc
V_{EB}	Emitter-Base Voltage	7.0	Vdc
I_C	Collector Current	1	Adc
P_D	Total Device Dissipation @T_A=25°C @T_C=25°C	 0.8 5.0	W
T_j	Junction Temperature	150	°C

Electrical Characteristics (T_{CASE}=25°C)

Off Characteristics

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
V_{CEO}(sus)	Collector-Emitter Sustaining Voltage I_C=30mAdc, I_B=0	90		Vdc
V_{CER}(sus)	Collector -Emitter sustaining Voltage I_C=100μAdc, R_{BE}=3.0KΩ	120		Vdc
I_{CBO}	Collector Cutoff Current V_{CB}=90Vdc, I_E=0		 .01	μAdc

On Characteristics

hFE	DC Current Gain I_C=150mAdc, V_{CE}=10Vdc	40	120	
V_{CE}	Collector-Emitter Saturation Voltage I_C=150mAdc, I_B=15mAdc		 0.3	Vdc
V_{BE}	Base-Emitter Saturation Voltage I_C=150mAdc, I_B=15mAdc		 1.1	Vdc

Dynamic Characteristics

f_T	Current-Gain-Bandwidth Product I_C=50mAdc, V_{CE}=10Vdc, f=5.0MHz		 50	MHz